Quad GTL/GTL+ to LVTTL/TTL bidirectional non-latched translator

Rev. 07 — 3 February 2009

Product data sheet

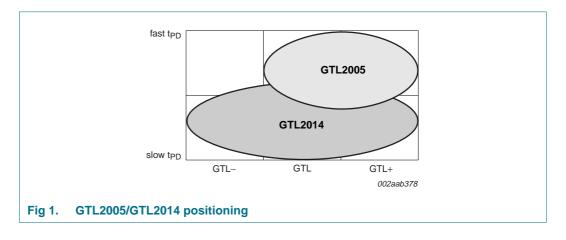
1. General description

The GTL2005 is a quad translating transceiver designed for 3.3 V system interface with a GTL/GTL+ bus.

The direction pin (DIR) allows the part to function as either a GTL-to-TTL sampling receiver or as a TTL-to-GTL interface.

The GTL2005 LVTTL interface is tolerant up to 5.5 V allowing direct access to TTL or 5 V CMOS outputs.

The GTL2005 V_{ref} linearity degrades below 0.8 V (see <u>Section 10.1</u>). If the application allows, use the GTL2014, otherwise more closely review noise margins.



2. Features

- Operates as a quad GTL/GTL+ sampling receiver or as a LVTTL/TTL to GTL/GTL+ driver
- Quad bidirectional bus interface
- 3.0 V to 3.6 V operation with 5 V tolerant LVTTL I/O
- Live insertion/extraction permitted
- Latch-up protection exceeds 500 mA per JESD78
- ESD protection exceeds 2000 V HBM per JESD22-A114, 150 V MM per JESD22-A115, and 1000 V CDM per JESD22-CC101
- Package offered: TSSOP14



Quick reference data 3.

Symbol	Parameter	Conditions	Min	Typ <mark>[1]</mark>	Max	Unit
Ci	input capacitance	control inputs; $V_1 = 3.0 V \text{ or } 0 V$	-	2.3	3.5	pF
C _{io}	input/output capacitance	A port; V _O = V _{TT} or 0 V	-	3.4	5.0	pF
		B port; V _O = 3.0 V or 0 V	-	6.0	7.0	pF
GTL; V _{ref}	= 0.8 V					
t _{PLH}	propagation delay, Bn to An	see Figure 7	-	2.1	2.3	ns
t _{PHL}			-	1.9	2.6	ns
t _{PLH}	propagation delay, An to Bn	see Figure 8	-	4.1	5.9	ns
t _{PHL}			-	4.4	5.9	ns

[1] All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

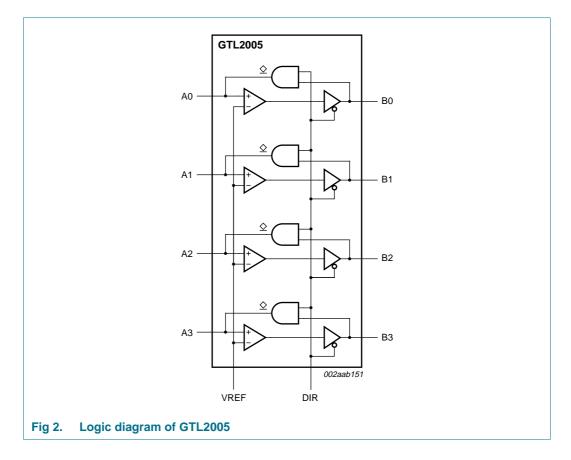
Ordering information 4.

Table 2.Ordering information $T_{amb} = -40 \degree C$ to $+85 \degree C$ Table 2.

Type number	Topside	Package				
	mark	Name	Description	Version		
GTL2005PW	GTL2005	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1		

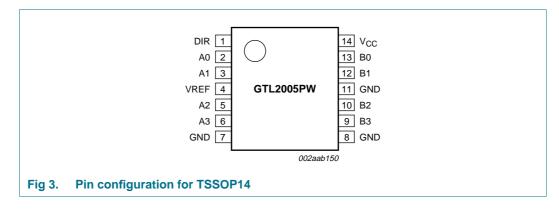
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5. Functional diagram



6. Pinning information

6.1 Pinning



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6.2 Pin description

SymbolPinDescriptionDIR1direction control inputA02data inputs/outputs (A side, GTL)A13A25A36B013data inputs/outputs (B side, TTL)B112B210B39VREF4GTL reference voltageGND7, 8, 11ground (0 V)Vec14positive supply voltage	Table 3.	Pin description		
A02data inputs/outputs (A side, GTL)A13A25A36B013data inputs/outputs (B side, TTL)B112B210B39VREF4GTL reference voltageGND7, 8, 11ground (0 V)	Symbol	Pin	Description	
A1 3 A2 5 A3 6 B0 13 B1 12 B2 10 B3 9 VREF 4 GTL reference voltage GND 7, 8, 11 ground (0 V)	DIR	1	direction control input	
A25A36B013data inputs/outputs (B side, TTL)B112B210B39VREF4GTL reference voltageGND7, 8, 11ground (0 V)	A0	2	data inputs/outputs (A side, GTL)	
A36B013data inputs/outputs (B side, TTL)B112B210B39VREF4GTL reference voltageGND7, 8, 11ground (0 V)	A1	3		
B013data inputs/outputs (B side, TTL)B112B210B39VREF4GTL reference voltageGND7, 8, 11ground (0 V)	A2	5		
B1 12 B2 10 B3 9 VREF 4 GTL reference voltage GND 7, 8, 11 ground (0 V)	A3	6		
B2 10 B3 9 VREF 4 GTL reference voltage GND 7, 8, 11 ground (0 V)	B0	13	data inputs/outputs (B side, TTL)	
B39VREF4GTL reference voltageGND7, 8, 11ground (0 V)	B1	12		
VREF4GTL reference voltageGND7, 8, 11ground (0 V)	B2	10		
GND 7, 8, 11 ground (0 V)	B3	9		
	VREF	4	GTL reference voltage	
V _{CC} 14 positive supply voltage	GND	7, 8, 11	ground (0 V)	
	V _{CC}	14	positive supply voltage	

7. Functional description

Refer to Figure 2 "Logic diagram of GTL2005".

7.1 Function table

Table 4.Function table

H = HIGH voltage level; L = LOW	voltage level.
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Input	Input/output		
DIR	B (TTL)	A (GTL)	
Н	inputs	Bn = An	
L	An = Bn	inputs	

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).^[1] Voltages are referenced to GND (ground = 0 V).

0		,			
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	DC supply voltage		-0.5	+4.6	V
I _{IK}	DC input diode current	V _I < 0 V	-	-50	mA
VI	DC input voltage	A port	-0.5 <mark>2]</mark>	+7.0	V
		B port	-0.5 <mark>2]</mark>	+4.6	V
I _{OK}	DC output diode current	V _O < 0 V	-	-50	mA
V _O	DC output voltage	output in OFF or HIGH state; A port	-0.5 <mark>[2]</mark>	+7.0	V
		output in OFF or HIGH state; B port	-0.5 <mark>[2]</mark>	+4.6	V
I _{OL}	current into any output in	B port	-	128	mA
	the LOW state	A port	-	80	mA
I _{OH}	current into any output in the HIGH state	B port	-	-64	mA
T _{stg}	storage temperature range		<u>[3]</u> –60	+150	°C

[1] Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under <u>Section 9 "Recommended operating conditions"</u> is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

[2] The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

[3] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150 °C.

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9. Recommended operating conditions

Table 6.	Operating conditions [1]	1					
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CC}	supply voltage			3.0	3.3	3.6	V
V _{TT}	termination voltage	GTL-		0.85	0.9	0.95	V
		GTL		1.14	1.2	1.26	V
		GTL+		1.35	1.5	1.65	V
V _{ref}	reference voltage	overall	[2]	0.5	$^{2}/_{3}V_{TT}$	1.8	V
		GTL-		0.5	0.6	0.63	V
		GTL		0.76	0.8	0.84	V
		GTL+		0.87	1.0	1.10	V
VI	input voltage	A port		0	V_{TT}	3.6	V
		except A port		0	3.3	5.5	V
VIH	HIGH-level input voltage	A port		[3]	-	-	V
		except A port		2	-	-	V
V _{IL}	LOW-level input voltage	A port		-	-	[3]	V
		except A port		-	-	0.8	V
I _{OH}	HIGH-level output current	B port		-	-	-12	mA
I _{OL}	LOW-level output current	A port		-	-	40	mA
		B port		-	-	12	mA
T _{amb}	ambient temperature	operating in free-air		-40	-	+85	°C

[1] Unused inputs must be held HIGH or LOW to prevent them from floating.

[2] V_{ref} is normally $\frac{2}{3}V_{TT}$, but based upon application and noise margin requirements can be set anywhere within this range and does not need to follow GTL-/GTL/GTL+ specification.

[3] Nominally $\pm 50 \text{ mV}$ around V_{ref}. See Figure 4, Figure 5, and Figure 6 for actual performance versus V_{ref}, V_{CC}, and temperature.

10. Static characteristics

Table 7. Static characteristics

Recommended operating conditions; voltages are referenced to GND (ground = 0 V); $T_{amb} = -40 \degree C$ to +85 °C.

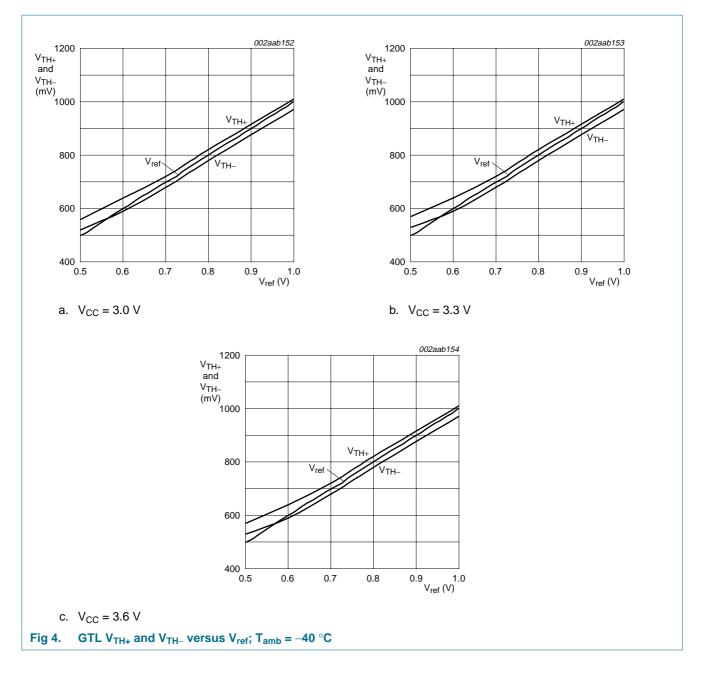
Symbol	Parameter	Conditions	l	Min	Typ <mark>[1]</mark>	Мах	Unit
V _{он}	HIGH-level output voltage	B port; V _{CC} = 3.0 V to 3.6 V; $I_{OH} = -100 \ \mu A$	[2] \	V _{CC} – 0.2	-	-	V
		B port; $V_{CC} = 3.0 V$; $I_{OH} = -12 \text{ mA}$	[2]	2.0	-	-	V
V _{OL}	LOW-level output	A port; V_{CC} = 3.0 V; I_{OL} = 40 mA	[2]	-	-	0.4	V
	voltage	B port; V_{CC} = 3.0 V; I_{OL} = 4 mA	[2]	-	-	0.4	V
		B port; V_{CC} = 3.0 V; I_{OL} = 8 mA	[2]	-	-	0.55	V
	B port; V_{CC} = 3.0 V; I_{OL} = 12 mA	[2]	-	-	0.8	V	
lı	input current	control inputs; $V_{CC} = 3.6 V$; $V_1 = V_{CC}$ or GND	-	-	-	±1	μA
	A port; $V_{CC} = 3.6 V$; $V_I = V_{TT}$ or GND	-	-	-	±1	μA	
		B port; $V_{CC} = 0$ V or 3.6 V; $V_1 = 5.5$ V	-	-	-	10	μA
		B port; V_{CC} = 3.6 V; V_{I} = V_{CC}	-	-	-	±1	μΑ
		B port; $V_{CC} = 3.6 \text{ V}; \text{ V}_{I} = 0 \text{ V}$	-	-	-	-5	μΑ
OFF	output OFF current	A port; $V_{CC} = 0 V$; V ₁ or V ₀ = 0 V to 4.5 V	-	-	-	±100	μΑ
EX	high contention over voltage leakage current	B port; V_{CC} = 3.0 V; V_{O} = 5.5 V	-	-	50	125	μA
сс	supply current	A or B port; $V_{CC} = 3.6 \text{ V}$; $V_I = V_{CC} \text{ or GND}$; $I_O = 0 \text{ mA}$	-	-	-	3	mA
∆I _{CC} [<u>3]</u>	additional supply current per input	B port or control inputs; V _{CC} = 3.6 V; V _I = V _{CC} - 0.6 V	-	-	-	500	μA
Ci	input capacitance	control inputs; $V_I = 3.0 \text{ V or } 0 \text{ V}$	-	-	2.3	3.5	pF
C _{io}	input/output	A port; $V_0 = V_{TT}$ or 0 V	-	-	3.4	5.0	pF
	capacitance	B port; $V_0 = 3.0$ V or 0 V	-	-	6.0	7.0	pF

[1] All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

[2] The input and output voltage ratings my be exceeded if the input and output current ratings are observed.

[3] This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

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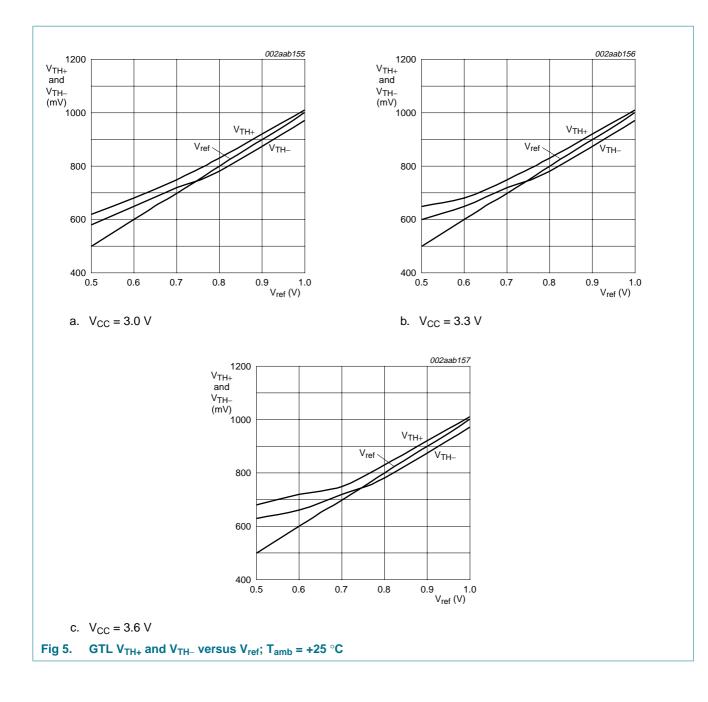


10.1 Performance curves

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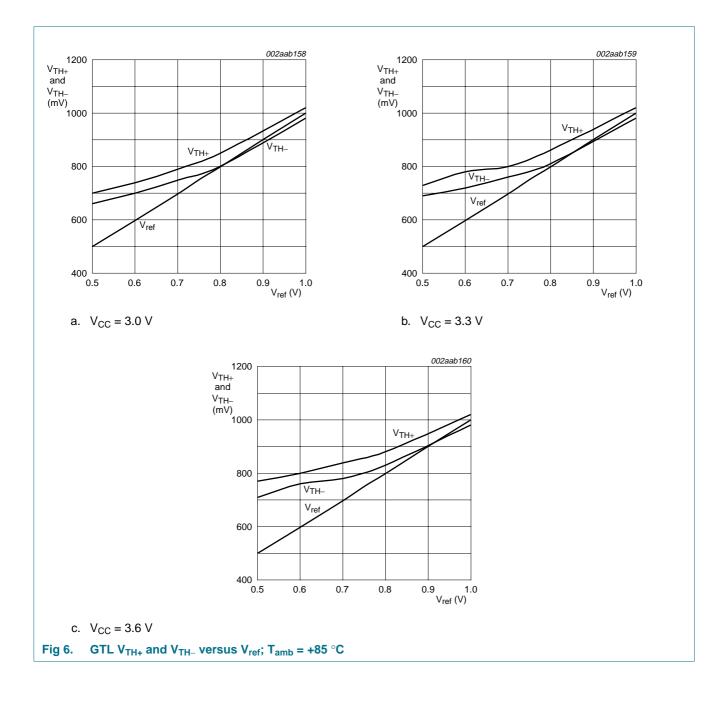
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11. Dynamic characteristics

Table 8. Dynamic characteristics

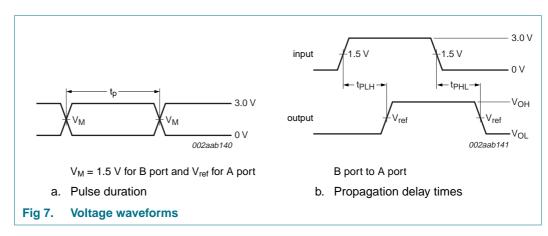
 $V_{CC} = 3.3 \ V \pm 0.3 \ V$

Parameter	Conditions	Min	Typ <mark>[1]</mark>	Мах	Unit
= 0.6 V					
propagation delay, Bn to An	see Figure 7	-	2.1	2.3	ns
		-	1.9	2.6	ns
propagation delay, An to Bn	see Figure 8	-	4.1	5.9	ns
		-	4.4	5.9	ns
GTL; V _{ref} = 0.8 V					
propagation delay, Bn to An	see Figure 7	-	2.1	2.3	ns
		-	1.9	2.6	ns
propagation delay, An to Bn	see Figure 8	-	4.1	5.9	ns
		-	4.4	5.9	ns
= 1.0 V					
propagation delay, Bn to An	see Figure 7	-	2.1	2.3	ns
		-	1.9	2.6	ns
propagation delay, An to Bn	see Figure 8	-	4.2	5.7	ns
		-	3.8	5.4	ns
	 = 0.6 V propagation delay, Bn to An propagation delay, An to Bn 0.8 V propagation delay, Bn to An propagation delay, An to Bn = 1.0 V propagation delay, Bn to An 	 = 0.6 V propagation delay, Bn to An see Figure 7 propagation delay, An to Bn see Figure 8 0.8 V propagation delay, Bn to An see Figure 7 propagation delay, An to Bn see Figure 8 = 1.0 V propagation delay, Bn to An see Figure 7 	 a 0.6 V propagation delay, Bn to An see Figure 7 propagation delay, An to Bn see Figure 8 	 a 0.6 V propagation delay, Bn to An see Figure 7 2.1 1.9 propagation delay, An to Bn see Figure 8 4.1 4.4 0.8 V propagation delay, Bn to An see Figure 7 2.1 1.9 propagation delay, An to Bn see Figure 8 4.1 4.4 I propagation delay, An to Bn see Figure 8 4.1 1.9 1.9 propagation delay, An to Bn see Figure 8 4.1 1.9 propagation delay, Bn to An see Figure 7 2.1 1.9 propagation delay, An to Bn see Figure 8 4.1 1.9 propagation delay, Bn to An see Figure 8 1.19 propagation delay, An to Bn see Figure 7 1.9 propagation delay, An to Bn see Figure 8 4.2 	= 0.6 V propagation delay, Bn to An see Figure 7 - 2.1 2.3 - 1.9 2.6 propagation delay, An to Bn see Figure 8 - 4.1 5.9 - 4.4 5.9 0.8 V - 4.4 5.9 propagation delay, Bn to An see Figure 7 - 2.1 2.3 propagation delay, An to Bn see Figure 7 - 2.1 2.3 propagation delay, An to Bn see Figure 8 - 4.1 5.9 = 1.9 2.6 - 1.9 2.6 propagation delay, An to Bn see Figure 8 - 4.1 5.9 = 1.0 V - 4.4 5.9 = 1.0 V - 1.9 2.6 propagation delay, Bn to An see Figure 7 - 2.1 2.3 - 1.9 2.6 - 1.9 2.6 propagation delay, An to Bn see Figure 8 - 4.2 5.7

[1] All typical values are at V_{CC} = 3.3 V and T_{amb} = 25 °C.

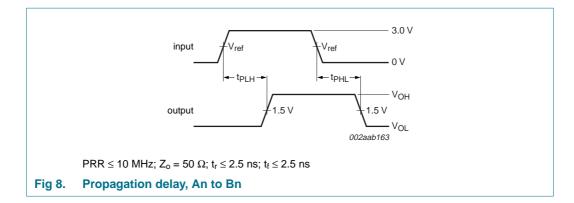
11.1 Waveforms

 V_M = 1.5 V at V_{CC} \geq 3.0 V; V_M = $V_{CC}/2$ at V_{CC} \leq 2.7 V for B ports and control pins; V_M = V_{ref} for A ports.

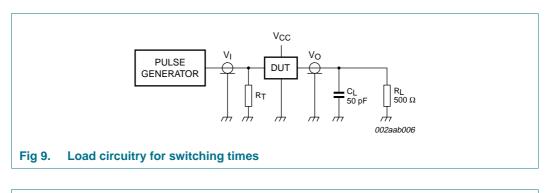


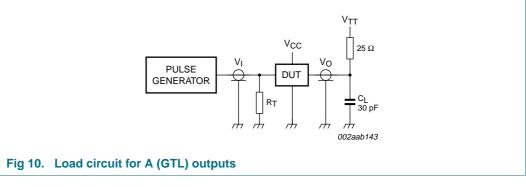
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12. Test information





- R_L Load resistor
- $\mathbf{C}_{\mathbf{L}}$ Load capacitance; includes jig and probe capacitance
- \mathbf{R}_{T} Termination resistance; should be equal to Z_{o} of pulse generators.

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13. Package outline

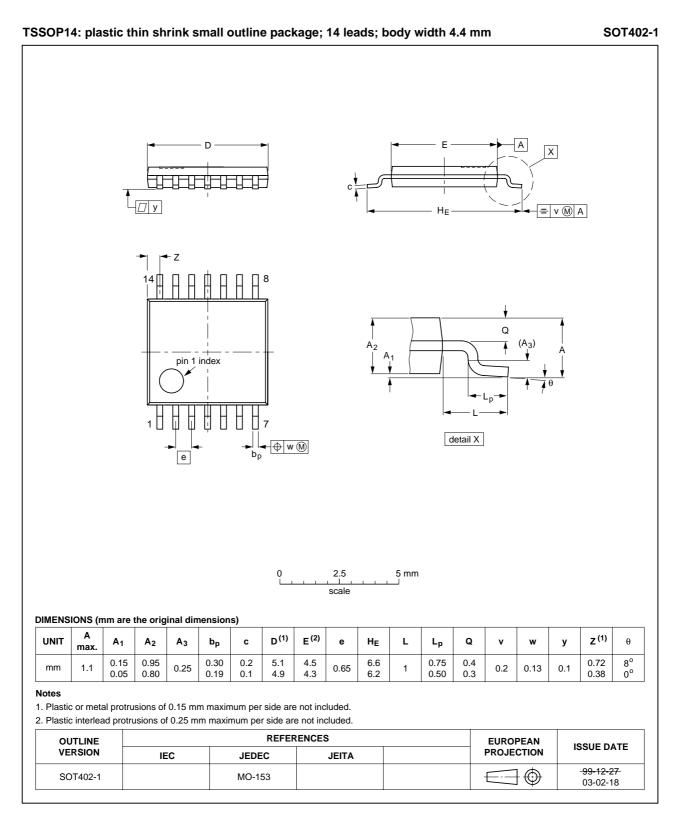


Fig 11. Package outline SOT402-1 (TSSOP14)

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14. Soldering of SMD packages

This text provides a very brief insight into a complex technology. A more in-depth account of soldering ICs can be found in Application Note *AN10365 "Surface mount reflow soldering description"*.

14.1 Introduction to soldering

Soldering is one of the most common methods through which packages are attached to Printed Circuit Boards (PCBs), to form electrical circuits. The soldered joint provides both the mechanical and the electrical connection. There is no single soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and Surface Mount Devices (SMDs) are mixed on one printed wiring board; however, it is not suitable for fine pitch SMDs. Reflow soldering is ideal for the small pitches and high densities that come with increased miniaturization.

14.2 Wave and reflow soldering

Wave soldering is a joining technology in which the joints are made by solder coming from a standing wave of liquid solder. The wave soldering process is suitable for the following:

- Through-hole components
- Leaded or leadless SMDs, which are glued to the surface of the printed circuit board

Not all SMDs can be wave soldered. Packages with solder balls, and some leadless packages which have solder lands underneath the body, cannot be wave soldered. Also, leaded SMDs with leads having a pitch smaller than ~0.6 mm cannot be wave soldered, due to an increased probability of bridging.

The reflow soldering process involves applying solder paste to a board, followed by component placement and exposure to a temperature profile. Leaded packages, packages with solder balls, and leadless packages are all reflow solderable.

Key characteristics in both wave and reflow soldering are:

- Board specifications, including the board finish, solder masks and vias
- · Package footprints, including solder thieves and orientation
- · The moisture sensitivity level of the packages
- Package placement
- Inspection and repair
- Lead-free soldering versus SnPb soldering

14.3 Wave soldering

Key characteristics in wave soldering are:

- Process issues, such as application of adhesive and flux, clinching of leads, board transport, the solder wave parameters, and the time during which components are exposed to the wave
- Solder bath specifications, including temperature and impurities

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14.4 Reflow soldering

Key characteristics in reflow soldering are:

- Lead-free versus SnPb soldering; note that a lead-free reflow process usually leads to higher minimum peak temperatures (see <u>Figure 12</u>) than a SnPb process, thus reducing the process window
- Solder paste printing issues including smearing, release, and adjusting the process window for a mix of large and small components on one board
- Reflow temperature profile; this profile includes preheat, reflow (in which the board is heated to the peak temperature) and cooling down. It is imperative that the peak temperature is high enough for the solder to make reliable solder joints (a solder paste characteristic). In addition, the peak temperature must be low enough that the packages and/or boards are not damaged. The peak temperature of the package depends on package thickness and volume and is classified in accordance with Table 9 and 10

Table 9. SnPb eutectic process (from J-STD-020C)

Package thickness (mm)	Package reflow temperature (°C)		
	Volume (mm ³)		
	< 350	≥ 350	
< 2.5	235	220	
≥ 2.5	220	220	

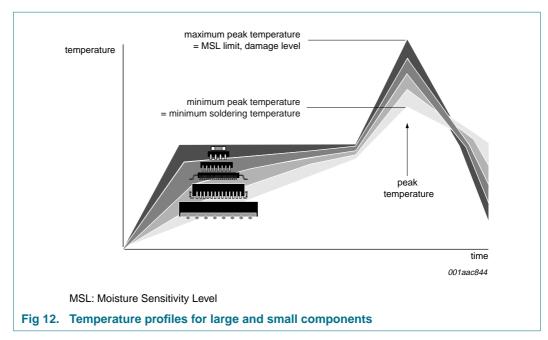
Table 10. Lead-free process (from J-STD-020C)

Package thickness (mm)	Package reflow temperature (°C)				
	Volume (mm ³)				
	< 350	350 to 2000	> 2000		
< 1.6	260	260	260		
1.6 to 2.5	260	250	245		
> 2.5	250	245	245		

Moisture sensitivity precautions, as indicated on the packing, must be respected at all times.

Studies have shown that small packages reach higher temperatures during reflow soldering, see Figure 12.

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For further information on temperature profiles, refer to Application Note AN10365 "Surface mount reflow soldering description".

15. Abbreviations

Table 11.	Abbreviations
Acronym	Description
CDM	Charged-Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
GTL	Gunning Transceiver Logic
HBM	Human Body Model
I/O	Input/Output
LVTTL	Low Voltage Transistor-Transistor Logic
MM	Machine Model
TTL	Transistor-Transistor Logic

16. Revision history

Table 12. Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes	
GTL2005_7	20090203	Product data sheet	-	GTL2005_6	
Modifications:	reversed	ic diagram of GTL2005" modifie	ed: symbol for AND gate	replaced and its direction	
GTL2005 6	20070906	Product data sheet	-	GTL2005 5	
			-		
GTL2005_5 (9397 750 14285)	20050406	Product data sheet	-	GTL2005_4	
GTL2005_4 (9397 750 13104)	20040510	Product data	-	GTL2005_3	
GTL2005_3 (9397 750 07222)	20000619	Product data	853-2171 23901	GTL2005_2	
GTL2005_2 (9397 750 06695)	19990917	Product data	853-2171 22353	GTL2005_1	
GTL2005_1 (9397 750 06497)	19990917	Product data		-	

17. Legal information

17.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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GTL2005

Quad GTL/GTL+ to LVTTL/TTL bidirectional non-latched translator

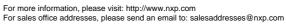
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